



## HIGH DENSITY MOUNTING PHOTOTRANSISTOR OPTICALLY COUPLED ISOLATORS

### DESCRIPTION

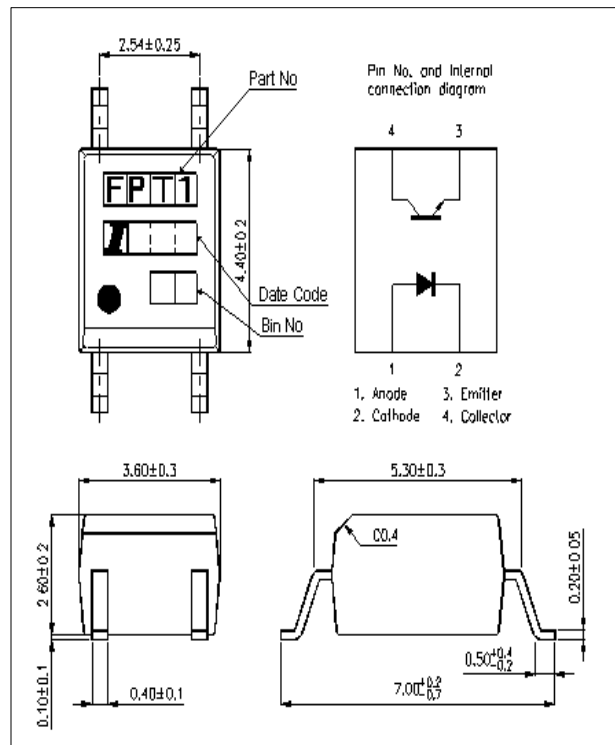
The IS357A is an optically coupled isolator consisting of an infrared light emitting diode and NPN silicon photo transistor in a space efficient dual in line plastic package.

### FEATURES

- Current Transfer Ratio 80 - 160 %
- Isolation Voltage (3.75kV<sub>RMS</sub>, 5.3kV<sub>PK</sub>)
- All electrical parameters 100% tested
- Custom electrical selections available
- Drop in replacement for Sharp PC357A

### APPLICATIONS

- Computer terminals
- Industrial systems controllers
- Measuring instruments
- Signal transmission between systems of different potentials and impedances



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**ABSOLUTE MAXIMUM RATINGS**  
(25°C unless otherwise specified)

Storage Temperature	-40°C to +125°C
Operating Temperature	-30°C to +100°C
Lead Soldering Temperature (1/16 inch (1.6mm) from case for 10 secs)	260°C

**INPUT DIODE**

Forward Current	50mA
Reverse Voltage	6V
Power Dissipation	70mW

**OUTPUT TRANSISTOR**

Collector-emitter Voltage $BV_{CEO}$	35V
Emitter-collector Voltage $BV_{ECO}$	6V
Power Dissipation	150mW

**POWER DISSIPATION**

Total Power Dissipation	170mW
(derate linearly 2.26mW/°C above 25°C)	

**ELECTRICAL CHARACTERISTICS (  $T_A = 25^\circ\text{C}$  Unless otherwise noted )**

PARAMETER		MIN	TYP	MAX	UNITS	TEST CONDITION
Input	Forward Voltage ( $V_F$ )		1.2	1.4	V	$I_F = 20\text{mA}$
	Reverse Voltage ( $V_R$ )	5			V	$I_R = 10\mu\text{A}$
	Reverse Current ( $I_R$ )			10	$\mu\text{A}$	$V_R = 4\text{V}$
Output	Collector-emitter Breakdown ( $BV_{CEO}$ )	35			V	$I_C = 0.5\text{mA}$
	Emitter-collector Breakdown ( $BV_{ECO}$ )	6			V	$I_E = 0.1\text{mA}$
	Collector-emitter Dark Current ( $I_{CEO}$ )			100	nA	$V_{CE} = 20\text{V}$
Coupled	Current Transfer Ratio (CTR)	80		160	%	$5\text{mA } I_F, 5\text{V } V_{CE}$
	Collector-emitter Saturation Voltage $V_{CE(SAT)}$			0.2	V	$20\text{mA } I_F, 1.0\text{mA } I_C$
	Input to Output Isolation Voltage $V_{ISO}$	3750 5300			$V_{RMS}$ $V_{PK}$	See note 1 See note 1
	Input-output Isolation Resistance $R_{ISO}$	$5 \times 10^{10}$			$\Omega$	$V_{IO} = 500\text{V}$ (note 1)
	Output Rise Time $t_r$		4	18	$\mu\text{s}$	$V_{CE} = 2\text{V}$ ,
Output Fall Time $t_f$		3	18	$\mu\text{s}$	$I_C = 2\text{mA}, R_L = 100\Omega$	

Note 1 Measured with input leads shorted together and output leads shorted together.

Note 2 Special Selections are available on request. Please consult the factory.

# CHARACTERISTIC CURVES

Fig.1 Forward Current vs. Ambient Temperature

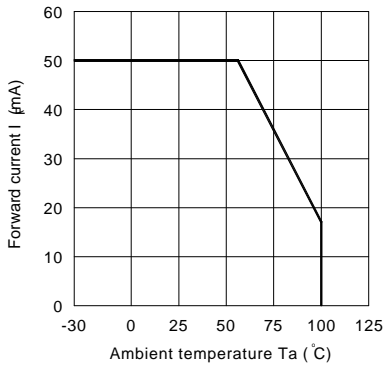


Fig.2 Collector Power Dissipation vs. Ambient Temperature

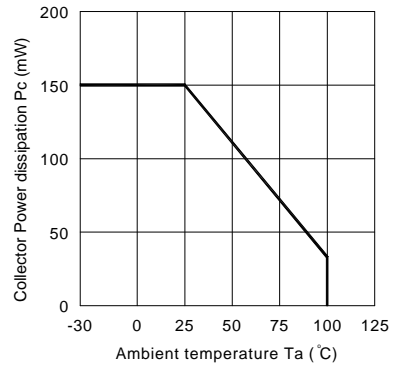


Fig.3 Collector-emitter Saturation Voltage vs. Forward Current

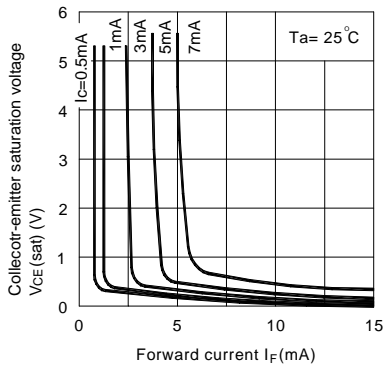


Fig.4 Forward Current vs. Forward Voltage

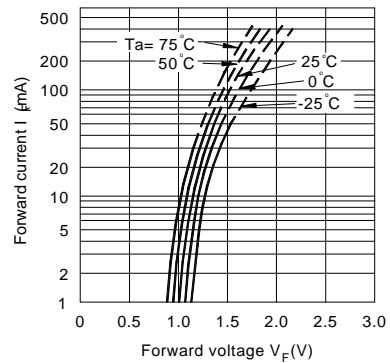


Fig.5 Current Transfer Ratio vs. Forward Current

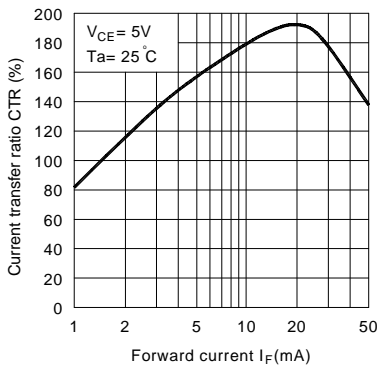
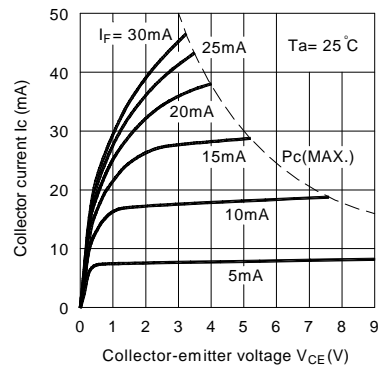


Fig.6 Collector Current vs. Collector-emitter Voltage



# CHARACTERISTIC CURVES

Fig.7 Relative Current Transfer Ratio vs. Ambient Temperature

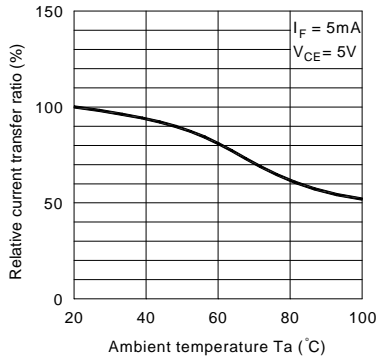


Fig.8 Collector-emitter Saturation Voltage vs. Ambient Temperature

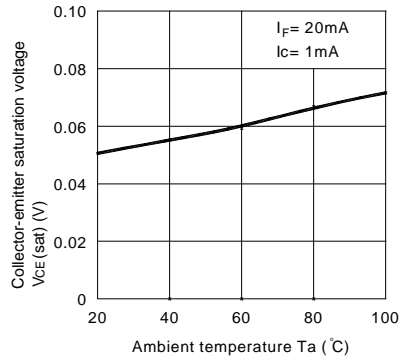


Fig.9 Collector Dark Current vs. Ambient Temperature

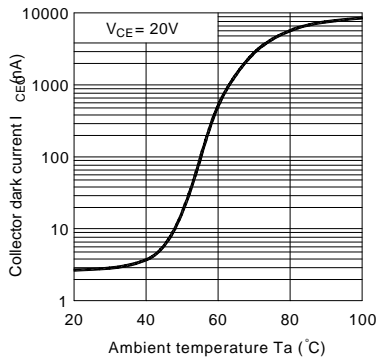


Fig.10 Response Time vs. Load Resistance

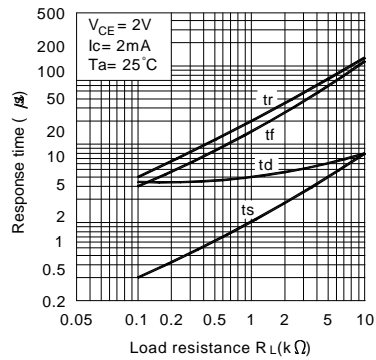
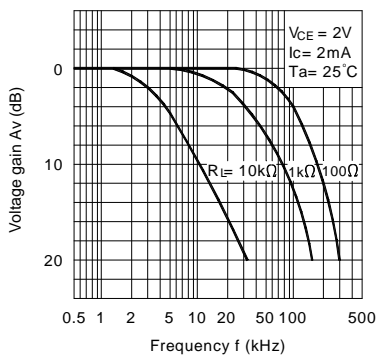
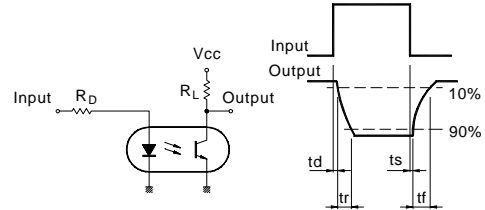


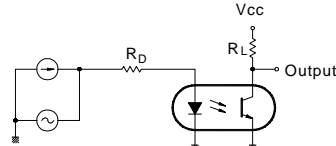
Fig.11 Frequency Response



Test Circuit for Response Time

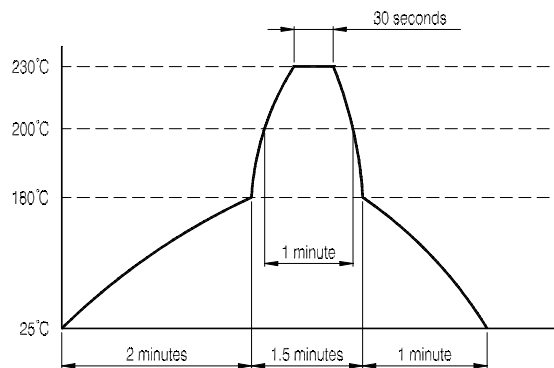


Test Circuit for Frequency Response



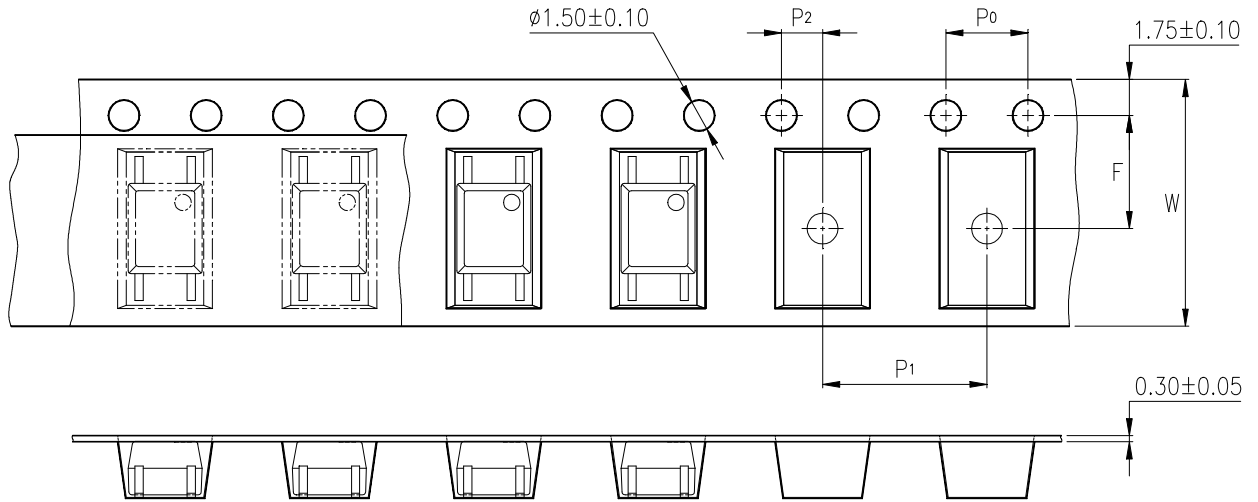
## TEMPERATURE PROFILE OF SOLDERING REFLOW

- (1) One time soldering reflow is recommended within the condition of temperature and time profile shown below.



- (2) When using another soldering method such as infrared ray lamp, the temperature may rise partially in the mold of the device.  
Keep the temperature on the package of the device within the condition of above (1).

## TAPING DIMENSIONS



Description	Symbol	Dimensions in mm ( inches )
Tape wide	W	12 ± 0.3 ( .47 )
Pitch of sprocket holes	P <sub>0</sub>	4 ± 0.1 ( .15 )
Distance of compartment	F	5.5 ± 0.1 ( .217 )
	P <sub>2</sub>	2 ± 0.1 ( .079 )
Distance of compartment to compartment	P <sub>1</sub>	8 ± 0.1 ( .315 )

This datasheet has been downloaded from:

[www.DatasheetCatalog.com](http://www.DatasheetCatalog.com)

Datasheets for electronic components.